Kun-Ming Chen

List of Publications by Year
in descending order

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15 papers	78 citations	1478505 6 h-index	1474206 9 g-index
15 all docs	15 docs citations	15 times ranked	92 citing authors

#	Article	IF	Citations
1	First Demonstration of Heterogeneous IGZO/Si CFET Monolithic 3-D Integration With Dual Work Function Gate for Ultralow-Power SRAM and RF Applications. IEEE Transactions on Electron Devices, 2022, 69, 2101-2107.	3.0	9
2	Effects of Channel Length on RF Performance of T-gate Poly-Si TFTs with Green Laser-Crystallized Channels. , 2022, , .		0
3	Extraction of Bias-dependent Source and Drain Resistances in AlGaN/GaN MIS-HEMTs Using Pulsed Measurement Method. ECS Journal of Solid State Science and Technology, 2022, 11, 065008.	1.8	0
4	AlInGaN/GaN HEMTs With High Johnsonâ€™s Figure-of-Merit on Low Resistivity Silicon Substrate. IEEE Journal of the Electron Devices Society, 2021, 9, 130-136.	2.1	7
5	Analysis of High-Frequency Behavior of AlGaN/GaN HEMTs and MIS-HEMTs under UV Illumination. ECS Journal of Solid State Science and Technology, 2021, 10, 055004.	1.8	1
6	Static and Radio-Frequency Characteristics of Green-Nanoseconds Laser-Crystallized Poly-Si Thin-Film Transistors. ECS Journal of Solid State Science and Technology, 2021, 10, 075010.	1.8	0
7	Comparison of X-parameter De-embedding Techniques for Intrinsic Large-Signal Characterization of Power FinFETs. , 2021, , .		0
8	Green Poly-Si TFTs: RF Breakthroughs $(f_{mathrm{T}}/f_{max}= 63.6/30 ext{GHz})$ by an Ingenious Process Design for IoT Modules on Everything. , 2021, , .		1
9	Study of Charge Trapping Effects on AlGaN/GaN HEMTs Under UV Illumination With Pulsed I-V Measurement. IEEE Transactions on Device and Materials Reliability, 2020, 20, 436-441.	2.0	19
10	Low-Frequency Noise Characterization of AlGaN/GaN HEMTs and MIS-HEMTs under UV Illumination. IEEE Nanotechnology Magazine, 2020, , 1-1.	2.0	7
11	A Unique Approach to Generate Self-Aligned T-Gate Transistors in Counter-Doped Poly-Si With High Etching Selectivity and Isotropy. IEEE Electron Device Letters, 2020, 41, 397-400.	3.9	5
12	Poly-Si Finlike Thin-Film Transistors With Various Wide Drain Designs for Radio Frequency and 3-D Integrated Circuits. IEEE Transactions on Electron Devices, 2020, 67, 2342-2345.	3.0	2
13	Large-Signal Characterization of Power FinFETs Based on X-Parameter Model. , 2019, , .		0
14	Analog and RF Characteristics of Power FinFET Transistors With Different Drain-Extension Designs. IEEE Transactions on Electron Devices, 2018, 65, 4225-4231.	3.0	15
15	Channel Thickness Effect on High-Frequency Performance of Poly-Si Thin-Film Transistors. IEEE Electron Device Letters, 2013, 34, 1020-1022.	3.9	12